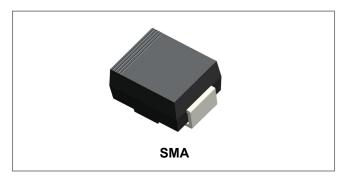


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# US1A THRU US1K SURFACE MOUNT ULTRA FAST RECTIFIER



#### **Features**

- Ideally Suited for Automatic Assembly
- Low Forward Overload Drop, High Efficiency
- Low Power Loss
- Super-Fast Recovery Time
- Plastic Material has UL Classification 94V-O
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

# **Circuit Diagram**



#### **Mechanical Data**

- Case: Low Profile Molded Plastic
- Terminals: Solder Plated, Solderable per MIL-STD-750, Method 2026
- Polarity: Cathode Band or Cathode Notch
- Weight: 0.06 grams(approx)

### Maximum Ratings and Electrical Characteristics @TA=25°C unless otherwise specified

Characteristic	Symbol	US1A	US1B	US1D	US1G	US1J	US1K	Units
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	50	100	200	400	600	800	V
RMS Reverse Voltage	V <sub>R(RMS)</sub>	35	70	140	280	420	560	] V
Average Rectified Output Current @T <sub>L</sub> =100°C	lo	1.0			Α			
Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I <sub>FSM</sub>	35				А		
Rating for fusing (t<8.3ms)	l²t	5.08			A <sup>2</sup> s			
Forward voltage @IF =1.0A	V <sub>F</sub>	1.0 1.3 1.7		7	V			
Peak Reverse Current @T <sub>A</sub> = 25°C At Rated DC Blocking Voltage @T <sub>A</sub> = 125°C	I <sub>R</sub>	5 200			μA			
Typical junction capacitance (Note 1)	Сл	45.0			pF			
Reverse Recovery Time (Note 2)	Trr	50 75		5	ns			
Typical thermal resistance (Note 3)	R <sub>θJA</sub>	30		°C/W				
Operating Junction and Storage Temperature Range	T <sub>J</sub> ,T <sub>STG</sub>	-55 to +150			°C			

Note: 1.Reverse Recovery Test Conditions: IF=0.5A, IR=1.0A, IRR=0.25A.

- 2. Measured at 1.0 MHz and Applied reverse Voltage of 4.0V D.C
- 3. 8.0mm<sup>2</sup> (.13mm Thick) Land Areas.
  - China Germany Korea Singapore United States
    - http://www.smc-diodes.com
       sales@ smc-diodes.com

### **US1A THRU US1K**

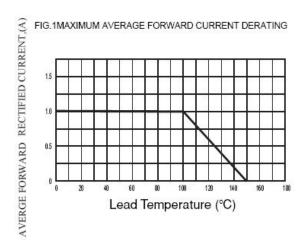


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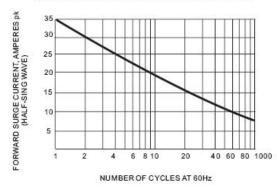




## **Ratings and Characteristics Curves**







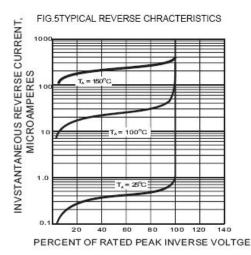


FIG.2TYPICAL FORWARD CHARACTERISTICS

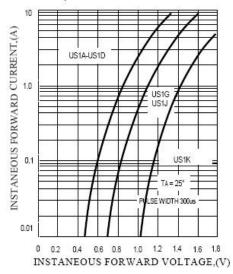
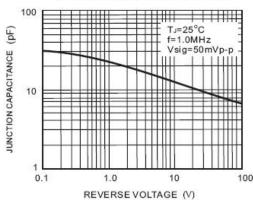
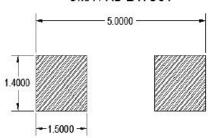


FIG.4TYPICAL JUNCTION CAPACITANCE



#### SMA PAD LAYOUT



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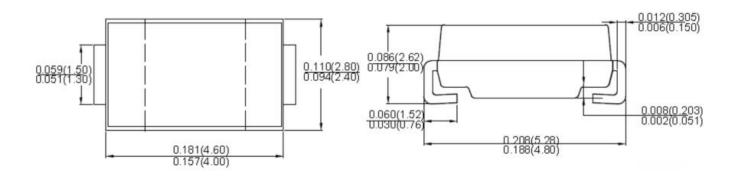
### **US1A THRU US1K**

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## **Mechanical Dimensions SMA (Inches/Millimeters)**



# **Ordering Information**

Device	Package	Shipping		
US1A				
THRU	SMA (Pb-Free)	5000pcs / reel		
US1K		·		

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

# **Marking Diagram**



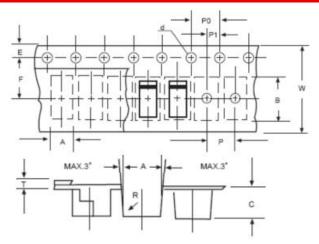
Where XXXXX is YYWWL

US = Device Type
1 = Forward Current (1A)
A = Reverse Voltage (50V)
YY = Year

WW = Week
L = Lot Number

**Cautions:** Molding resin Epoxy resin UL:94V-0

# **Carrier Tape Specification SMA**



SYMBOL	Millimeters			
	Min.	Max.		
Α	2.97	3.17		
В	5.70	5.90		
O	2.32	2.52		
d	1.40	1.60		
E	1.40	1.60		
F	5.60	5.70		
Р	3.90	4.10		
P0	3.90	4.10		
P1	1.90	2.10		
T	0.25	0.35		
W	11.80	12.20		

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#### **US1A THRU US1K**

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